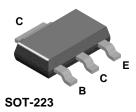


BCP54



NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switching circuits requiring collector currents to 1.2 A. Sourced from Process 38.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V _{CBO}	Collector-Base Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	1.5	Α
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BCP54	
P_{D}	Total Device Dissipation	1.5	W
	Derate above 25°C	12	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	83.3	°C/W

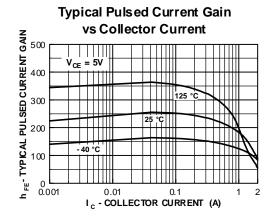
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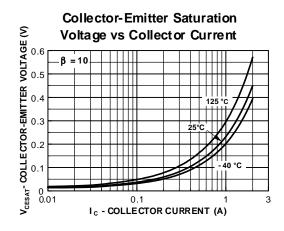
NPN General Purpose Amplifier

(continued)

Electrical Characteristics TA = 25°C unless otherwise noted							
Symbol	Parameter	Test Conditions	Min	Max	Units		
OFF CHA	RACTERISTICS						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	45		V		
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	45		V		
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V		
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		100	nA		
		$V_{CB} = 30 \text{ V}, I_E = 0, T_A = 125^{\circ}\text{C}$		10	μΑ		
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		10	μΑ		
ON CHAR	ACTERISTICS						
h_{FE}	DC Current Gain	$I_C = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V}$	25				
		$I_C = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}$	40 25	250			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	25	0.5	V		
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$		1.0	V		

Typical Characteristics

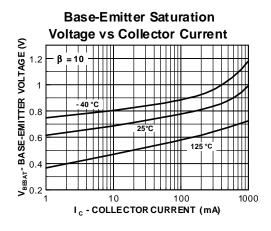


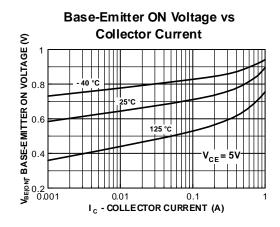


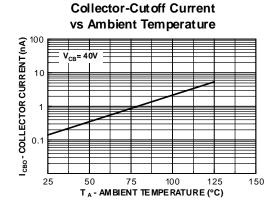
NPN General Purpose Amplifier

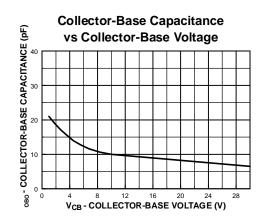
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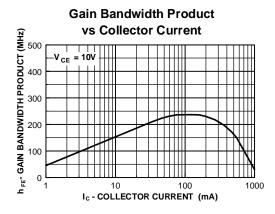
Typical Characteristics (continued)

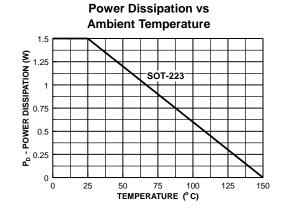


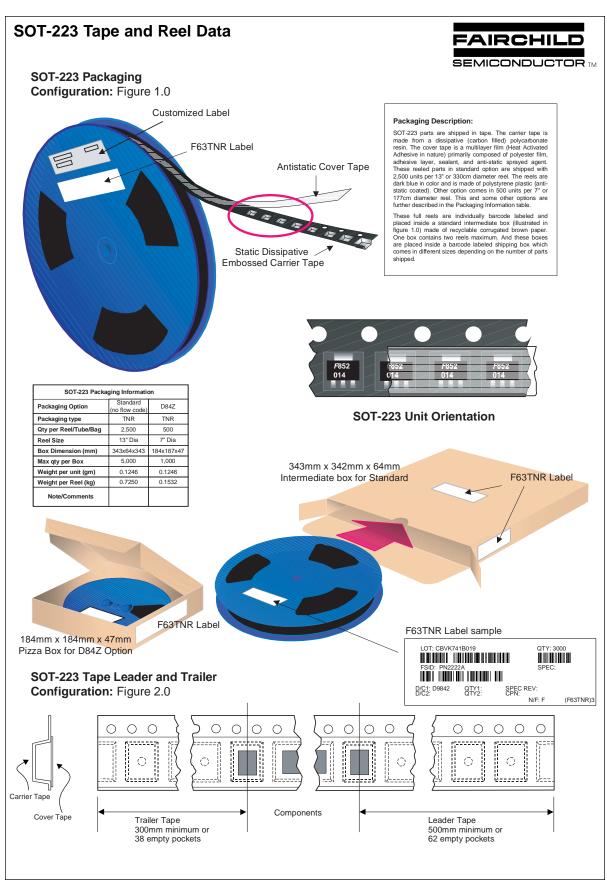






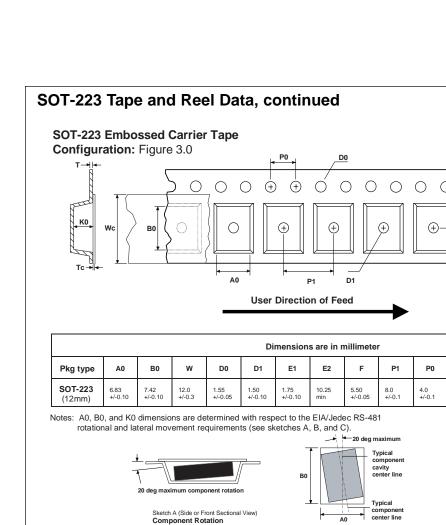


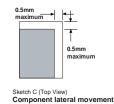




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0.292 +/-0.0130

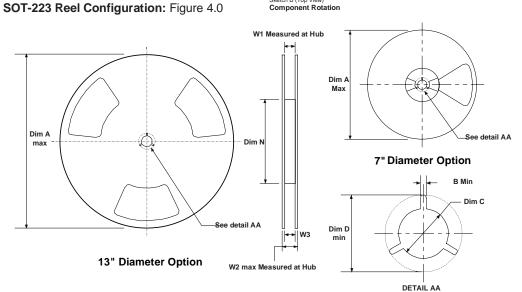
Wc

Tc

0.06 +/-0.02

K0

Sketch B (Top View)
Component Rotation



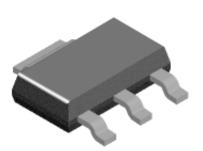
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

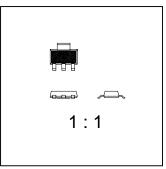
July 1999, Rev. B

SOT-223 Package Dimensions



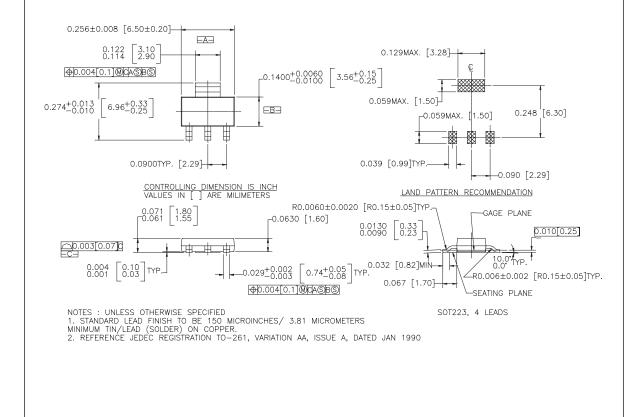
SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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September 1999, Rev. C

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Datasheet Identification	Product Status	Definition
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Rev. G